

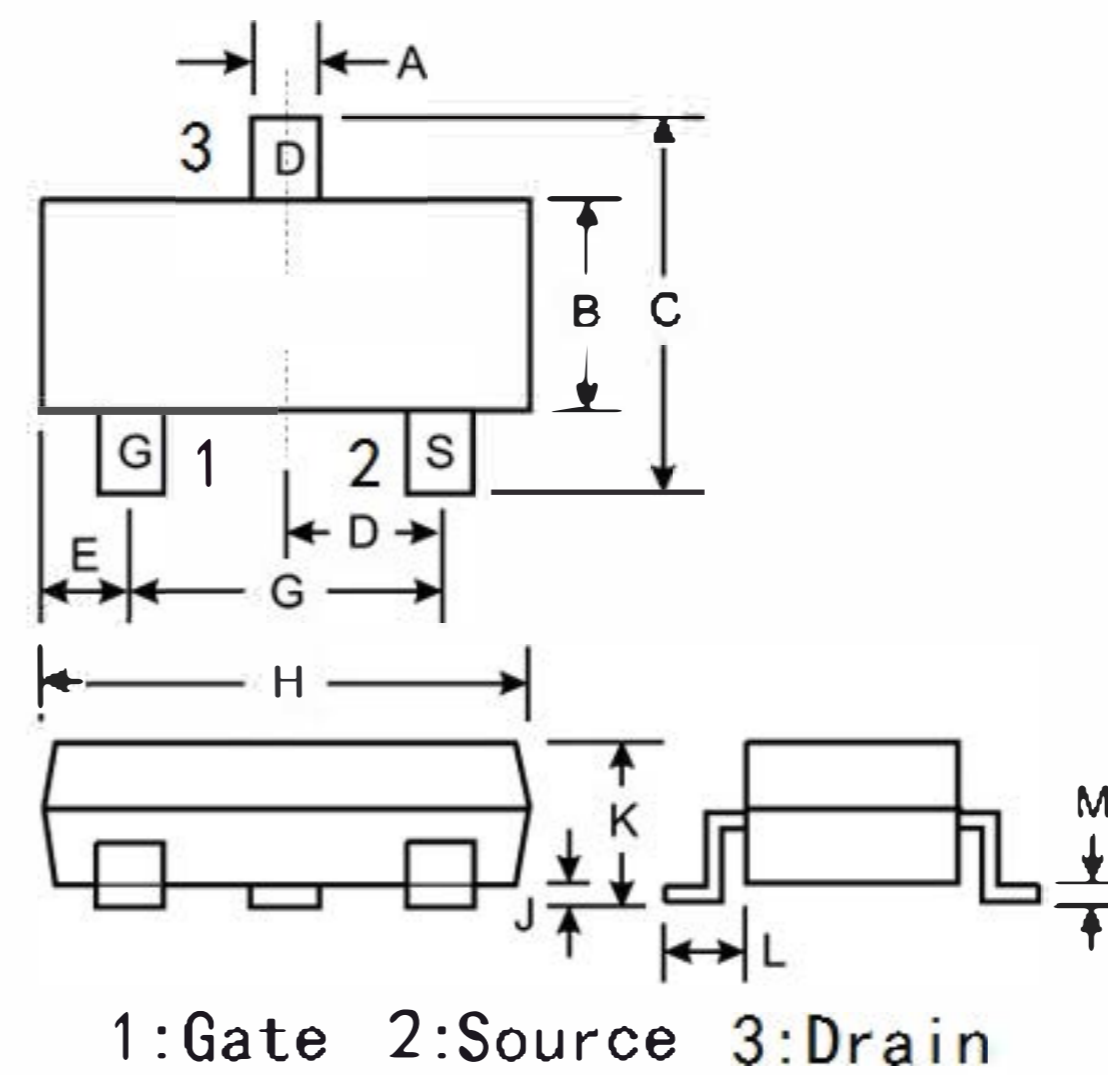
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

● Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected up to 1kV(HBM)

● Mechanical Data

- Case: SOT-323, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approx.)



SOT-323		
Dim	Min	Max
A	0.30	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

● Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	2N7002W	Units
Drain-Source Voltage	V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ	V _{DGR}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Pulsed		±40	
Drain Current (Note 1)	I _D	115	mA
Continuous		73	
Continuous @ 100°C Pulsed		800	
Total Power Dissipation (Note 1) Derating above T _A = 25°C	P _d	200	mW
		1.60	mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	625	K/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

- Note: 1. Valid provided that terminals are kept at specified ambient temperature.
2. Pulse width ≤ 300μs, duty cycle ≤ 2%.

● **Electrical Characteristics** @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	70	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0 500	μA	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ $V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	—	—	± 5	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	3.2 4.4	7.5 13.5	Ω	@ $T_{j} = 25^\circ\text{C}$ @ $T_{j} = 125^\circ\text{C}$ $V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current	$I_{D(on)}$	0.5	1.0	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	g_{FS}	80	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	22	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	11	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.0	5.0	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	—	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$ $R_L = 150\Omega, V_{GEN} = 10V,$ $R_{GEN} = 25\Omega$
Turn-Off Delay Time	$t_{D(OFF)}$	—	11	20	ns	

Note: 1. Valid provided that terminals are kept at specified ambient temperature.
2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

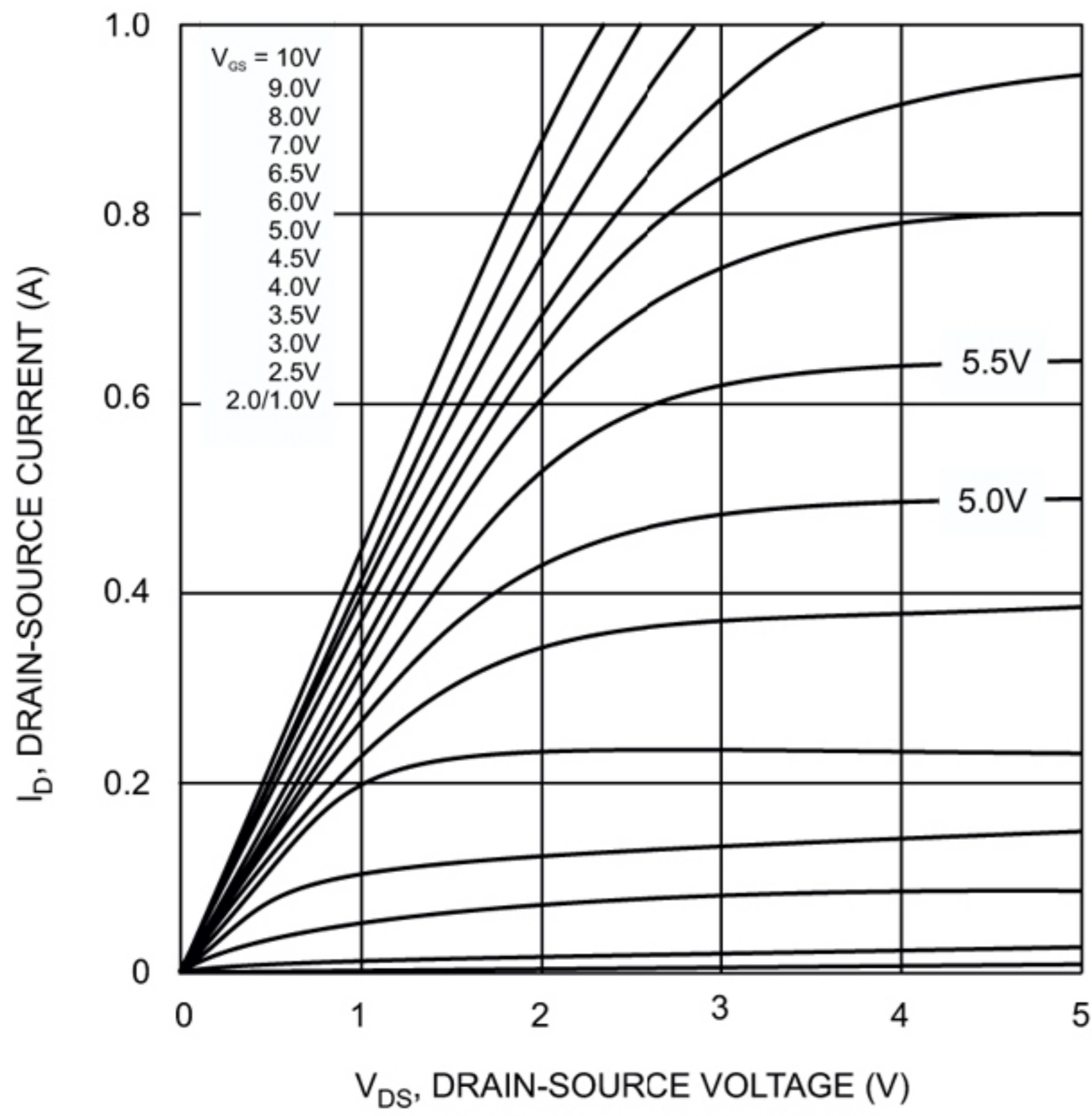


Fig. 1 On-Region Characteristics

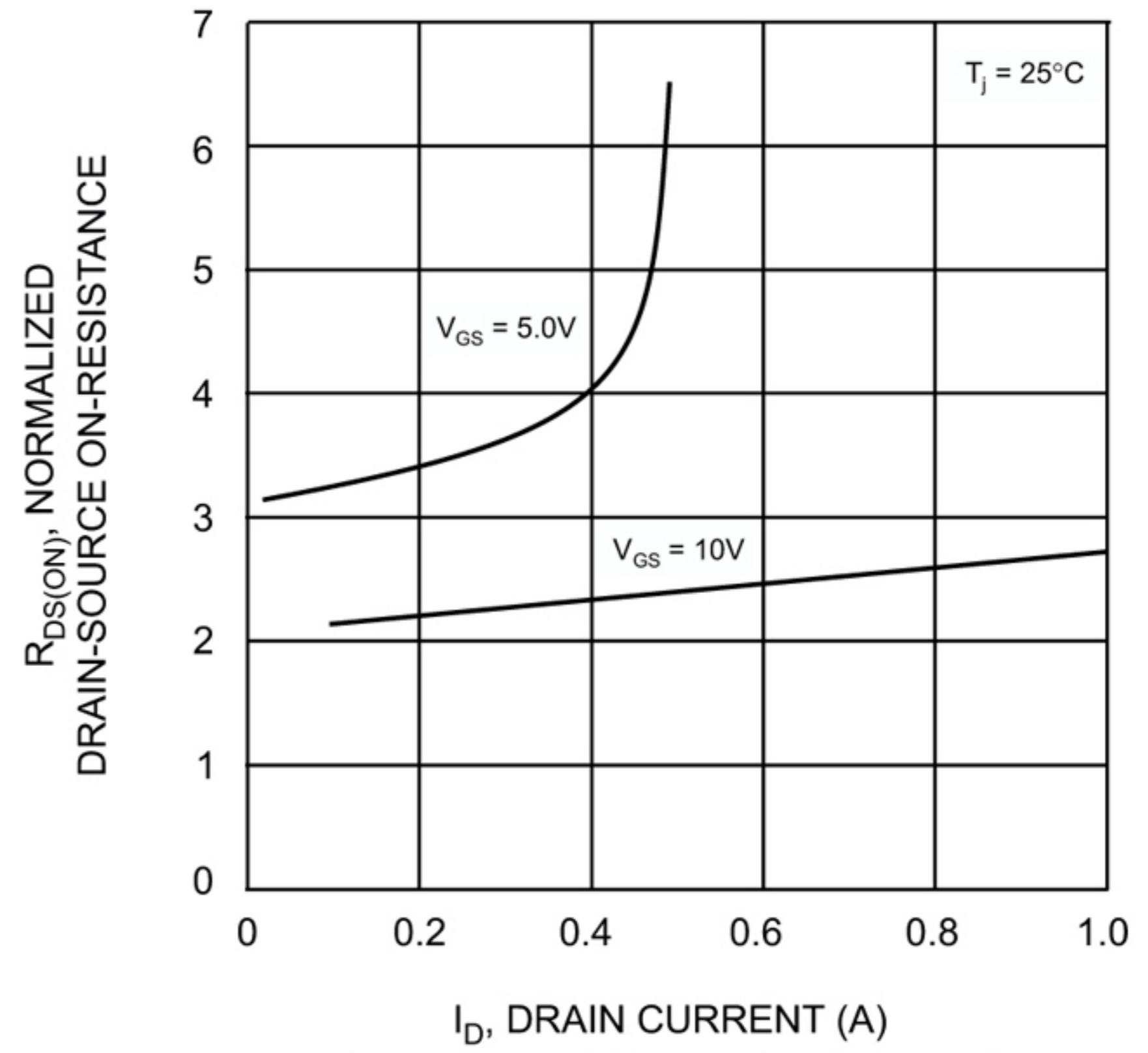


Fig. 2 On-Resistance vs Drain Current

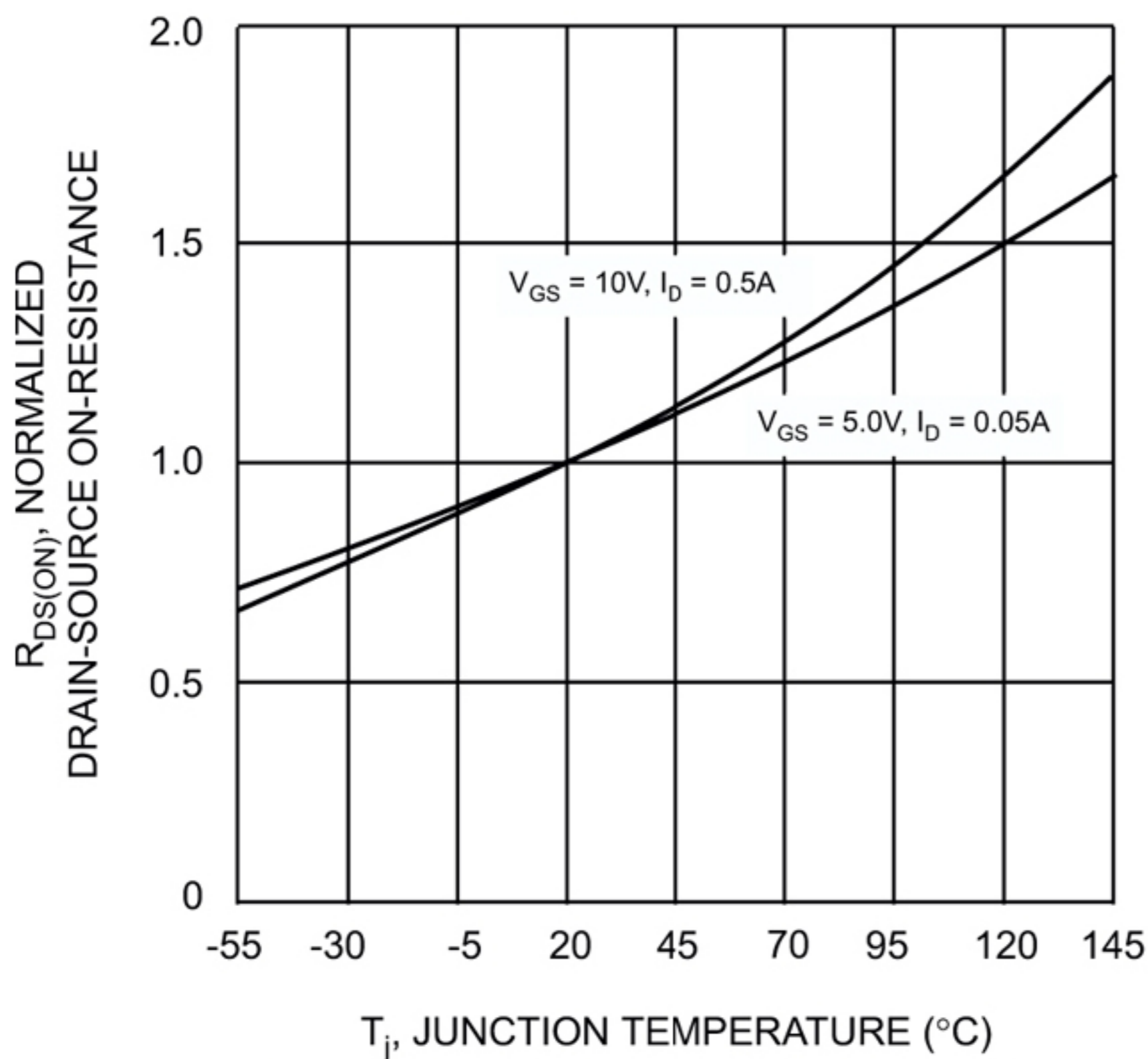


Fig. 3 On-Resistance vs Junction Temperature

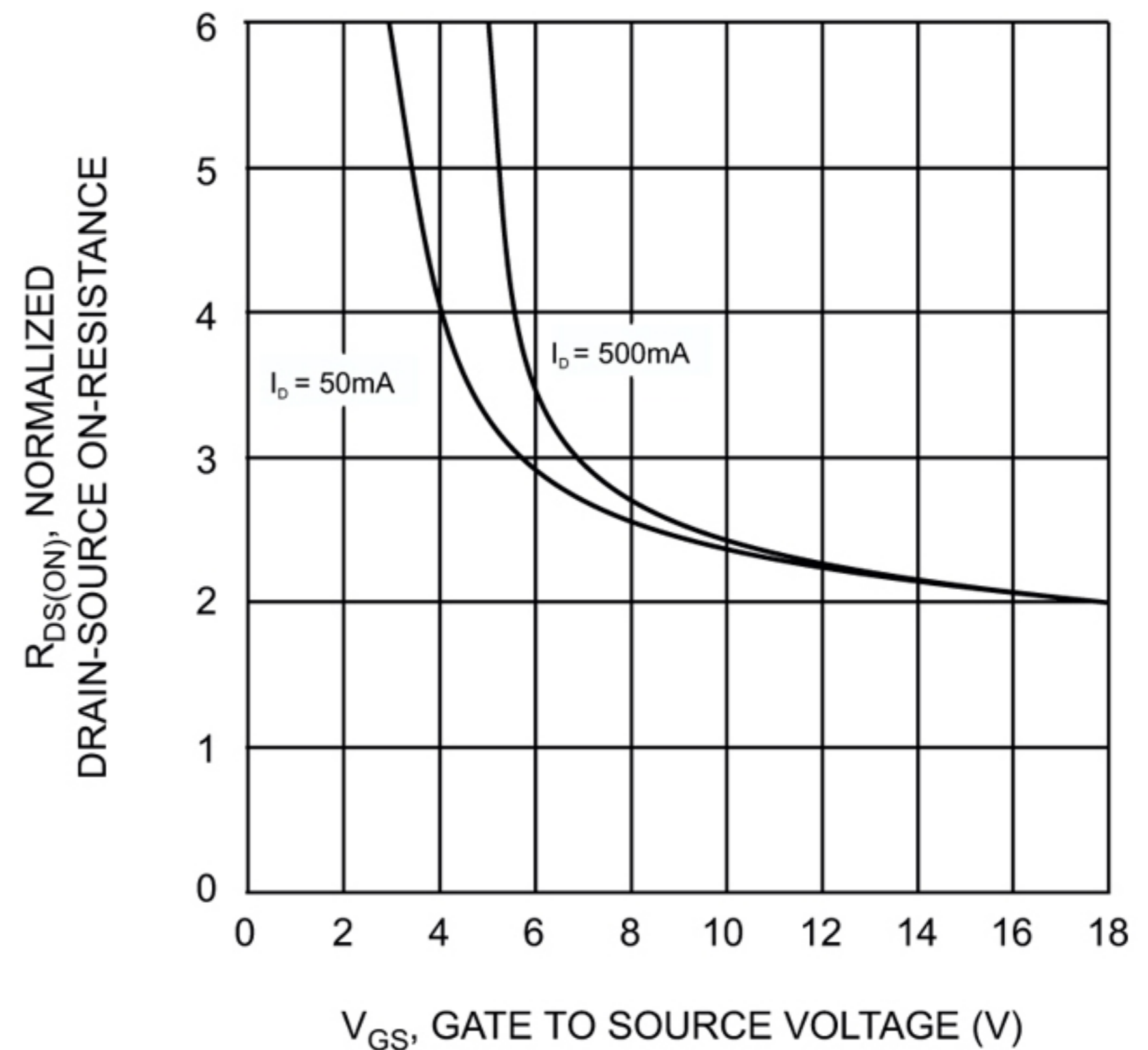


Fig. 4 On-Resistance vs. Gate-Source Voltage

单击下面可查看定价，库存，交付和生命周期等信息

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